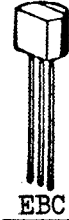


BC 537 · BC 538

NPN SILICON AF MEDIUM POWER TRANSISTORS

THE BC537, BC538 ARE NPN SILICON PLANAR EPITAXIAL TRANSISTORS FOR USE IN AF DRIVER AND OUTPUT STAGES, AS WELL AS FOR UNIVERSAL APPLICATIONS. THE BC537, BC538 ARE COMPLEMENTARY TO THE PNP TYPE BC527, BC528 RESPECTIVELY.

CASE TO-92A



ABSOLUTE MAXIMUM RATINGS

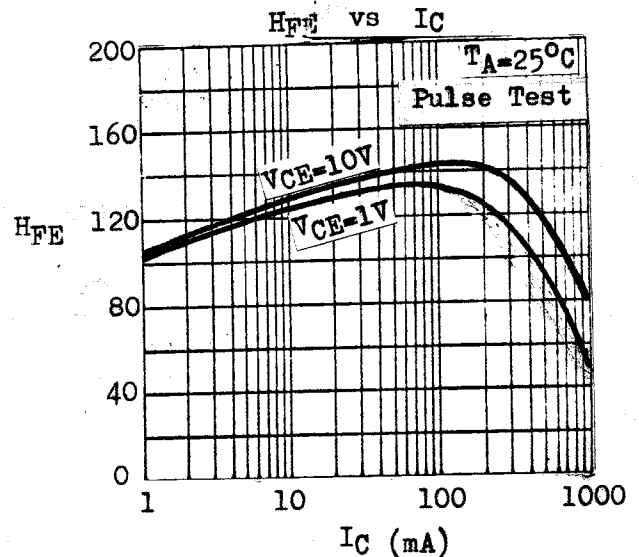
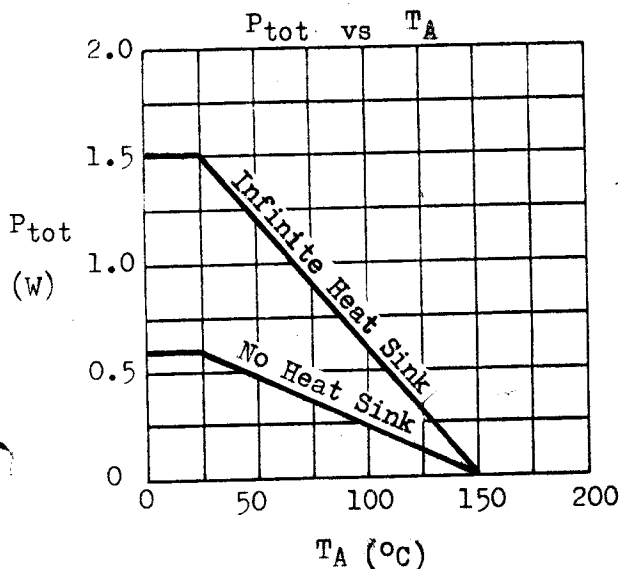
Collector-Base Voltage
 Collector-Emitter Voltage
 Emitter-Base Voltage
 Collector Current
 Collector Peak Current ($t \leq 10\text{ms}$)
 Total Power Dissipation (@ $T_C \leq 25^\circ\text{C}$)
 (@ $T_A \leq 25^\circ\text{C}$)
 Operating Junction & Storage Temperature

	BC537	BC538
VCBO	60V	80V
VCEO	60V	80V
VEBO		6V
IC		1A
ICM		1.5A
Ptot		1.5W
		625mW
Tj, Tstg	-55 to 150°C	

THERMAL RESISTANCE

Junction to Case
 Junction to Ambient

θ_{jc}	83°C/W max.
θ_{ja}	200°C/W max.



MICRO ELECTRONICS LTD.

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 TELEPHONE:- 3-430181-6 3-893369, 3-892423
 FAX: 3-410321

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	BC537		BC538		UNIT	TEST CONDITIONS	
		MIN	MAX	MIN	MAX			
Collector-Base Breakdown Voltage	BV_{CBO}	60		80		V	$I_C=0.1\text{mA}$ $I_E=0$	
Collector-Emitter Breakdown Voltage	$LV_{CEO} *$	60		80		V	$I_C=10\text{mA}$ $I_B=0$	
Emitter-Base Breakdown Voltage	BV_{EBO}	6		6		V	$I_E=0.01\text{mA}$ $I_C=0$	
Collector Cutoff Current	I_{CBO}		100			nA	$V_{CB}=40\text{V}$ $I_E=0$	
					100	nA	$V_{CB}=60\text{V}$ $I_E=0$	
Emitter Cutoff Current	I_{EBO}		100		100	nA	$V_{EB}=4\text{V}$ $I_C=0$	
Collector-Emitter Saturation Voltage	$V_{CE(sat)} *$		0.7		0.7	V	$I_C=500\text{mA}$ $I_B=50\text{mA}$	
			1.2		1.5	V	$I_C=1\text{A}$ $I_B=0.1\text{A}$	
Base-Emitter Saturation Voltage	$V_{BE(sat)} *$		1.3		1.3	V	$I_C=150\text{mA}$ $I_B=15\text{mA}$	
D.C. Current Gain	$H_{FE} *$	40	400	40	400		$I_C=100\text{mA}$ $V_{CE}=1\text{V}$	
		Group 6	40	100	40	100		
		Group 10	63	160	63	160		
		Group 16	100	250	100	250		
		Group 25	160	400	160	400		
		All Groups	$H_{FE} *$	50		50		$I_C=10\text{mA}$ $V_{CE}=10\text{V}$
		50		50		$I_C=150\text{mA}$ $V_{CE}=10\text{V}$		
		50		50		$I_C=500\text{mA}$ $V_{CE}=10\text{V}$		
		15		15		$I_C=1\text{A}$ $V_{CE}=10\text{V}$		
Current Gain-Bandwidth Product	f_T	100		100		MHz	$I_C=50\text{mA}$ $V_{CE}=10\text{V}$	
Collector-Base Capacitance	C_{ob}		15		15	pF	$V_{CB}=10\text{V}$ $I_E=0$ $f=1\text{MHz}$	

* Pulse Test : Pulse Width=0.3mS, Duty Cycle=1%

